

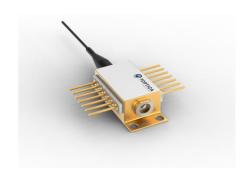
2023-01-17

TAPERED AMPLIEIER



IAI LILLO AIVII L	-11 11-17	
Semiconductor	Optical	Amplifier

roduct	Application
50 nm Tapered Amplifier	Spectroscopy
Pin Butterfly Package (non hermetic)	



Absolute Maximum Ratings

General Product Information

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T _S	° C	-40		85
Operational Temperature at Case	T _C	°C	-20		75
Forward Current	I _F	А			3.5
Reverse Voltage	V_R	V			2
Output Power	P _{opt}	W			2.2
TEC Current	I_{TEC}	А			5
TEC Voltage	V_{TEC}	V			7

Measurement Conditions / Comment	iS
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Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _{case}	°C	0		50
Operational Temperature at Chip	T_LD	°C	10	25	35
Forward Current	I _F	А			3.2
Input Power	P _{opt}	mW	10		50
Output Power	Popt	W			2

Measurement Conditions / Comments
seeding required above 1.6 A
with proper injection from a seed laser

Characteristics at T	− 25 °C at BOI

Parameter	Symbol	Unit	min	typ	max
Wavelength	λ	nm		850	
Gain Width (FWHM)	$\Delta\lambda$	nm		20	
Output Power	P _{opt}		2		
Polarization				TE	
Amplification	G	dB		16	
Temp. Coefficient of Wavelength	dλ/dT	nm/K		0.3	

Measurement Conditions / Comments
E field parallel to base plate



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Characteristics at T _{LD}	= 25 °C at BOL				cont'd
Parameter	Symbol	Unit	min	typ	max
Beam Diameter	d	mm		1	
Output Divergence parallel	Θ_{out}	mrad		3	
Output Divergence perpendicular	$\Theta_{\text{out}\perp}$	mrad		3	

Measurement Conditions / Comments
1/e²
1/e² (full angle)
1/e² (full angle)

Thermoelectric Cooler					
Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		1.2	
Voltage	U_{TEC}	V		2	
Power Dissipation (total loss at case)	P _{loss}	W		8	
Temperature Difference	ΔΤ	K			40

Measurement Conditions / Comments
Popt '= 2 W; DT '= 20 K
Popt '= 2 W; DT '= 20 K
Popt '= 2 W; DT '= 20 K
Popt '= 2 W



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Thermistor (Standard NTC Type)				
Parameter	Symbol	Unit m	in typ	max
Resistance	R		10	
Beta Coefficient	b		3892	
Steinhart & Hart Coefficient A	А		1.1293 x 1	0 -3
Steinhart & Hart Coefficient B	В		2.3410 x 1	0 -4
Steinhart & Hart Coefficient C	С		8.7755 x 1	0 -8

Measurement Conditions / Comments
25° C
0° 50° C



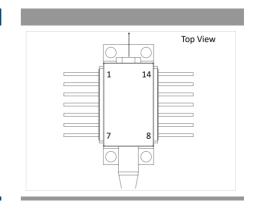


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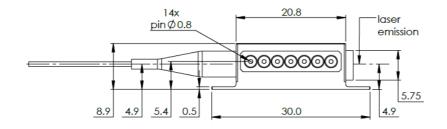
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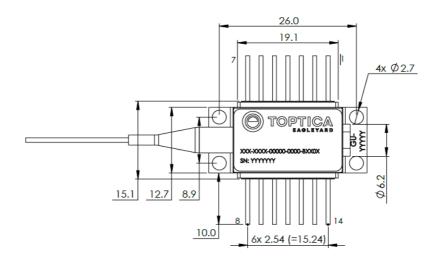
Pin Assignment	
1 Thermoelectric Cooler (+)	14 Thermoelectric Cooler (-)
2 Thermistor	13 not connected
3 not connected	12 not connected
4 not connected	11 Amplifier (Cathode)
5 Thermistor	10 Amplifier (Anode)
6 not connected	9 not connected
7 not connected	8 not connected



Package Drawings







Caution. Excessive mechanical stress on the package can lead to a damage of the laser.

See instruction manual on www.toptica-eagleyard.com

SWZ-23-0117-1237





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Fiber and Connector Type (Input)					
Parameter					
PM Fiber	900 / 125 / 5.5 μm, UV/Polyester-elastomer Coating				
	length: 1 +/-0.1 m				
Connector	FC/APC				
	narrow key / 2 mm				
	narrow key / 2 mm				

Measurement Conditions / Comments



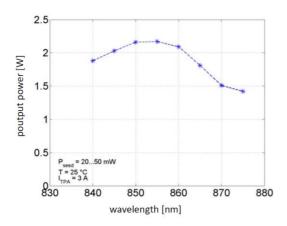
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TAPERED AMPLIFIER Semiconductor Optical Amplifier



Typical Measurement Results

output power with seeding at different wavelengths



Unpacking, Installation and Laser Safety

Unpacking the taperd amplifier should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TPA diode type is known to be sensitive against thermal stress. It should not be operated without appropriate injection from a seed laser. Operating at moderate temperatures on proper heat sinks willI contribute to a long lifetime of the diode.

This amplifier is designed for the setup of MOPA systems. Appropriate seed lasers are DFB lasers of the $type\ EYP-DFB-xxxx-xxxxx-1500-xxxxx-000x\ with\ matching\ wavelengths.\ An\ external\ fiber\ isolator\ should$ be used between seed laser and amplifier in order to suppress backreflections that may disturb the

Each tapered amplifier will come with an individual test protocol verifying the parameters given in this document.











with 21 CFR 1040.10 and 1040.40